

Vishay Semiconductors

# Medium Power Silicon Rectifier Diodes, (Stud Version), 12 A



PRIMARY CHARACTERISTICS				
I <sub>F(AV)</sub>	12 A			
Package	DO-4 (DO-203AA)			
Circuit configuration	Single			

#### **FEATURES**

- Voltage ratings from 50 V to 1000 V
- · High surge capability



- Low thermal impedance
- High temperature rating
- Can be supplied as JAN and JAN-TX devices in accordance with MIL-S-19500/260
- Material categorization: for definitions of compliance please see <a href="https://www.vishay.com/doc?99912"><u>www.vishay.com/doc?99912</u></a>

MAJOR RATINGS AND CHARACTERISTICS				
PARAMETER	TEST CONDITIONS	VALUES	UNITS	
I <sub>F(AV)</sub>		12	A	
	T <sub>C</sub>	150	°C	
I <sub>FSM</sub>	50 Hz	230	^	
	60 Hz	240	Α	
I <sup>2</sup> t	50 Hz	260	A <sup>2</sup> s	
	60 Hz	240	A-5	
T <sub>J</sub>		-65 to +200	°C	
V <sub>RRM</sub>	Range	50 to 1000	V	

#### Note

#### **ELECTRICAL SPECIFICATIONS**

VOLTAGE RA	VOLTAGE RATINGS				
TYPE NUMBER	V <sub>RRM</sub> , MAXIMUM REPETITIVE PEAK REVERSE VOLTAGE (T <sub>C</sub> = -65 °C TO 200 °C) V	V <sub>R(RMS)</sub> , MAXIMUM RMS REVERSE VOLTAGE (T <sub>C</sub> = -65 °C TO 200 °C) V	V <sub>RSM</sub> , MAXIMUM NON-REPETITIVE PEAK REVERSE VOLTAGE (T <sub>C</sub> = -65 °C TO 200 °C) V	V <sub>RM</sub> , MAXIMUM DIRECT REVERSE VOLTAGE (T <sub>C</sub> = -65 °C TO 200 °C) V	
VS-1N1199A	50	35	100	50	
VS-1N1200A	100	70	200	100	
VS-1N1201A	150	105	300	150	
VS-1N1202A	200	140	350	200	
VS-1N1203A	300	210	450	300	
VS-1N1204A	400	280	600	400	
VS-1N1205A	500	350	700	500	
VS-1N1206A	600	420	800	600	
VS-1N3670A	700	490	900	700	
VS-1N3671A	800	560	1000	800	
VS-1N3672A	900	630	1100	900	
VS-1N3673A	1000	700	1200	1000	
VS-1N3624	1000	1200	1400	1000	

#### Notes

- JEDEC® registered values are in bold
- Basic part number indicates cathode to case; for anode to case, add "R" to part number, e.g., 1N1199RA

JEDEC® registered values are in bold



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FORWARD COM	IDUCTION					
PARAMETER		SYMBOL	TEST CONDITIONS		VALUES	UNITS
Maximum average forward current at case temperature		I <sub>F(AV)</sub>	180° sinusoidal conduction		12	Α
		·F(AV)	Too sinassiaa sonaasiisi		150	°C
Maximum peak one cycle non-repetitive surge current		I <sub>FSM</sub>	Half cycle 50 Hz sine wave or 6 ms rectangular pulse	Following any rated load condition and with rated V <sub>RRM</sub> applied	230	
			Half cycle 60 Hz sine wave or 5 ms rectangular pulse		240	
			Half cycle 50 Hz sine wave or 6 ms rectangular pulse	Following any rated load	275	
			Half cycle 60 Hz sine wave or 5 ms rectangular pulse	condition and with V <sub>RRM</sub> applied following surge = 0 V	285	
			t = 10 ms	With rated V <sub>RRM</sub> applied	260	
Maximum I <sup>2</sup> t for fusin	Maximum I <sup>2</sup> t for fusing		t = 8.3 ms	following surge, initial T <sub>J</sub> = 200 °C	240	A <sup>2</sup> s
Maximum I2t for indiv	Maximum I <sup>2</sup> t for individual		t = 10 ms	With V <sub>RRM</sub> = 0 V following	370	
device fusing			t = 8.3 ms	surge, initial T <sub>J</sub> = 200 °C	340	]
Maximum I <sup>2</sup> √t for indi device fusing	Maximum I <sup>2</sup> √t for individual device fusing		t = 0.1 ms to 10 ms, V <sub>RRM</sub> = 0 V following surge		3715	A²√s
Maximum forward voltage drop		$V_{FM}$	I <sub>F(AV)</sub> = 12 A (38 A peak), T <sub>C</sub> = 25 °C		1.35	V
	V <sub>RRM</sub> = 50 V		· · · · · · · · · · · · · · · · · · ·		3.0	
	V <sub>RRM</sub> = 100 V				2.5	
	V <sub>RRM</sub> = 150 V				2.25	]
	$V_{RRM} = 200 \text{ V}$	I <sub>R(AV)</sub> <sup>(2)</sup>	Maximum rated $I_{F(AV)}$ and $T_{C}$		2.0	mA
Maximum average reverse current	V <sub>RRM</sub> = 300 V				1.75	
	V <sub>RRM</sub> = 400 V				1.5	
	$V_{RRM} = 500 \text{ V}$				1.25	
	$V_{RRM} = 600 \text{ V}$				1.0	
	$V_{RRM} = 700 \text{ V}$				0.9	
	$V_{RRM} = 800 \text{ V}$				8.0	
	V <sub>RRM</sub> = 900 V				0.7	-
	V <sub>RRM</sub> = 1000 V				0.6	

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- (1)  $I^2t$  for time  $t_x = I^2\sqrt{t} \times \sqrt{t_x}$
- (2) Maximum peak reverse current ( $I_{RM}$ ) under same conditions  $\approx 2 \text{ x rated } I_{R(AV)}$

THERMAL AND MECHANICAL SPECIFICATIONS					
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum operating ca storage temperature ra		T <sub>C</sub> , T <sub>Stg</sub>		-65 to 200	°C
Maximum internal thermal resistance, junction to case		$R_{thJC}$	DC operation	2.0	°C/W
Thermal resistance, case to sink		R <sub>thCS</sub>	Mounting surface, smooth, flat and greased 0.5		
	minimum		Torque applied to nut; non-lubricated threads	1.36 (12)	N · m (lbf · in)
	maximum			1.69 (15)	
Mounting torque	minimum		Tarana analiad ta mutulularia ataul thuasada	1.07 (9.45)	
Mounting torque	maximum		Torque applied to nut; lubricated threads	1.30 (11.55)	
	minimum		Torque applied to device case; lubricated threads	1.17 (10.35)	
	maximum			1.43 (12.65)	
Approximate weight				7.0	g
				0.25	OZ.
Case style			JEDEC® DO-4 (DO-203A		D-203AA)

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## Vishay Semiconductors

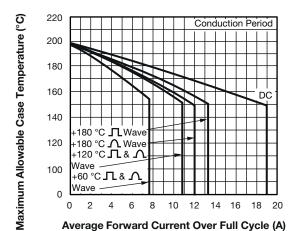


Fig. 1 - Average Forward Current vs. Maximum Allowable Case Temperature

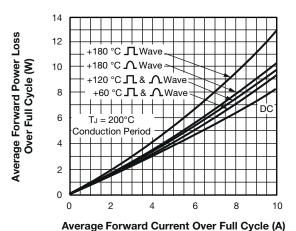


Fig. 2 - Maximum Low Level Forward Power Loss vs. Average Forward Current

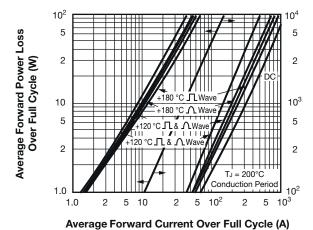


Fig. 3 - Maximum High Level Forward Power Loss vs. Average Forward Current

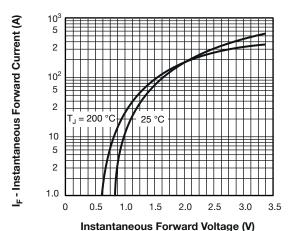


Fig. 4 - Maximum Forward Voltage vs. Forward Current

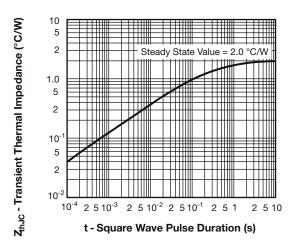


Fig. 5 - Maximum Transient Thermal Impedance, Junction to Case vs. Pulse Duration

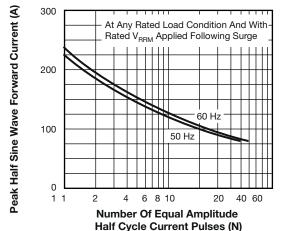


Fig. 6 - Maximum Non-Repetitive 50 Hz Surge Current vs. Number of Current Pulses

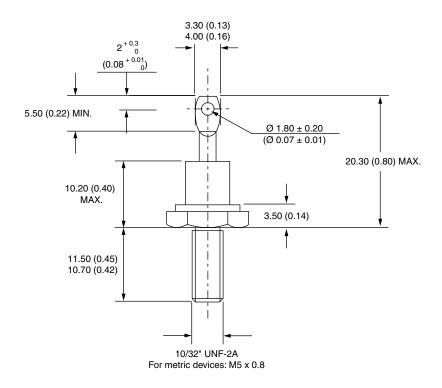
LINKS TO RELATED DOCUMENTS		
Dimensions	www.vishay.com/doc?95311	

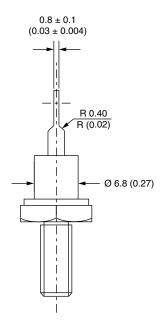


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# DO-203AA (DO-4)

### **DIMENSIONS** in millimeters (inches)







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